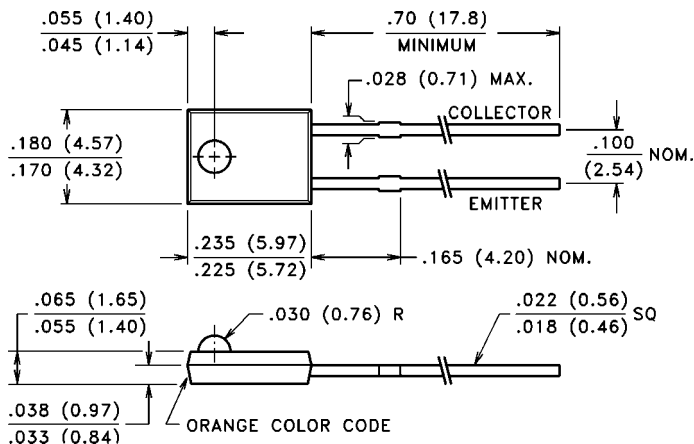


PACKAGE DIMENSIONS inch (mm)



**CASE 7 LATERAL
 CHIP TYPE: 25T**

PRODUCT DESCRIPTION

A small area high speed NPN silicon phototransistor mounted in a lensed, side looking, transparent plastic, transfer molded package. These devices are spectrally and mechanically matched to the VTE717xH series of IREDs.

ABSOLUTE MAXIMUM RATINGS ■

(@ 25°C unless otherwise noted)

Maximum Temperatures	
Storage Temperature:	-40°C to 85°C
Operating Temperature:	-40°C to 85°C
Continuous Power Dissipation:	50 mW
Derate above 30°C:	0.91 mW/°C
Maximum Current:	25 mA
Lead Soldering Temperature:	260°C
	(1.6 mm from case, 5 sec. max.)

RoHS Compliant



ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also typical curves, pages 91-92)

Part Number	Light Current		Dark Current		Collector Breakdown	Emitter Breakdown	Saturation Voltage	Rise/Fall Time	Angular Response $\theta_{1/2}$	
	I_C		I_{CEO}		$V_{BR(CEO)}$	$V_{BR(ECO)}$	$V_{CE(SAT)}$	t_r/t_f		
	mA	H	H = 0		$I_C = 100 \mu A$ H = 0	$I_E = 100 \mu A$ H = 0	$I_C = 1.0 mA$ H = 400 fc	$I_C = 1.0 mA$ $R_L = 100 \Omega$		
	Min.	Max.	fc (mW/cm ²) $V_{CE} = 5.0 V$	(nA) Max.	V_{CE} (Volts)	Volts, Min.	Volts, Min.	Volts, Max.		μsec , Typ.
VTT7122H	1.0	—	100 (5)	100	10	30	5.0	0.25	2.0	$\pm 36^\circ$
VTT7123H	2.0	—	100 (5)	100	10	30	5.0	0.25	2.0	$\pm 36^\circ$
VTT7125H	4.5	—	100 (5)	100	10	30	5.0	0.25	2.0	$\pm 36^\circ$

■ Refer to General Product Notes, page 2.